查询BC328供应商

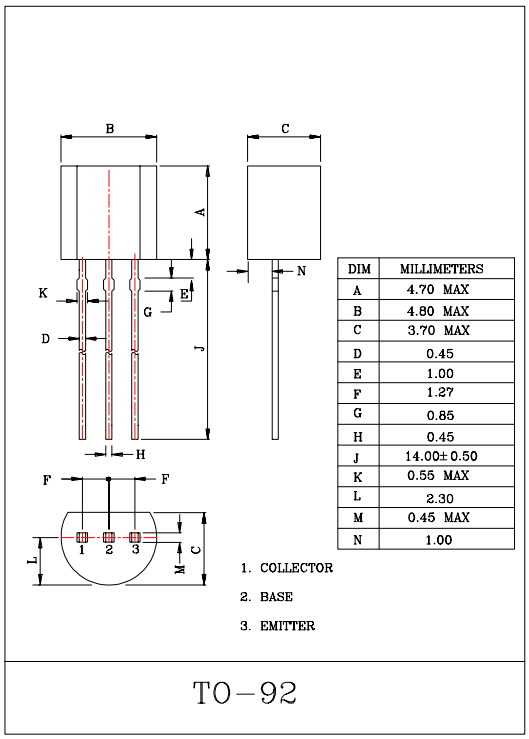
KOREA ELECTRONICS CO.,LTD.

SEMICONDUCTOR
TECHNICAL DATA

BC328
EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEATURES
- High Current : I_C=-800mA.
- DC Current Gain : h_{FE}=100～400 (V_{CE}=-1V, I_c=-100mA).
- For Complementary with NPN type BC338.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

TO-92

MAXIMUM RATINGS (Ta=25℃)

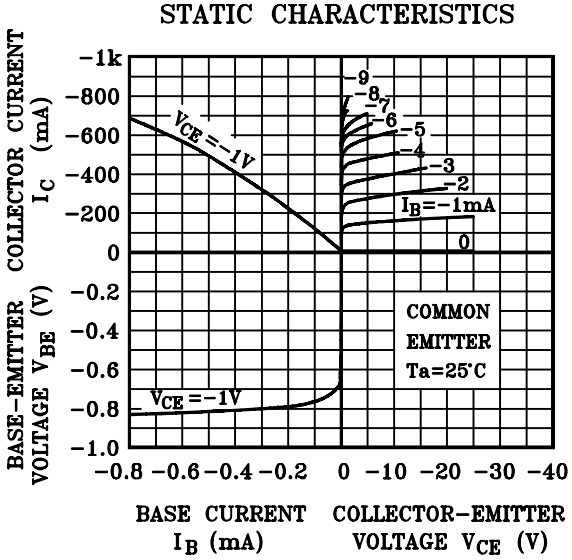
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Emitter Current	I_E	800	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

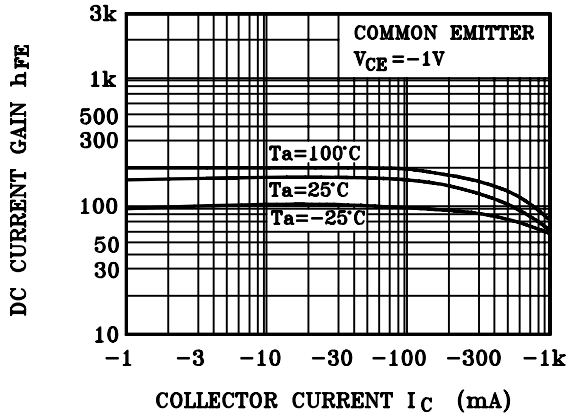
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-25V, I_E=0	-	-	-100	nA
DC Current Gain (Note)	h_{FE}	V_{CE}=-1V, I_C=-100mA	100	-	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA	-	-	-0.7	V
Base-Emitter Voltage	$V_{BE(ON)}$	V_{CE}=-1V, I_C=-300mA	-	-	-1.2	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-10mA, f=100MHz	-	100	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, f=1MHz	-	16	-	pF

Note : h_{FE} Classification none:100～400 , 16:100～250 , 25:160～400

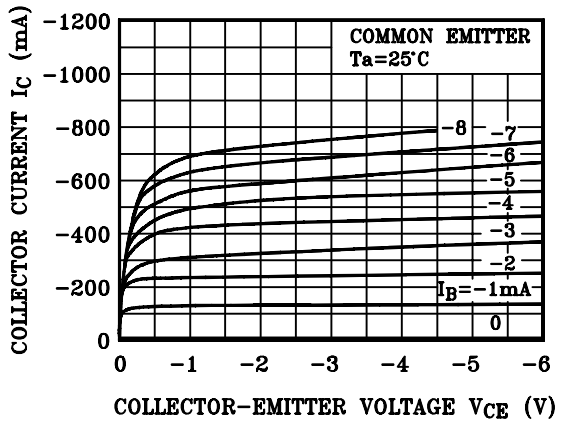
STATIC CHARACTERISTICS



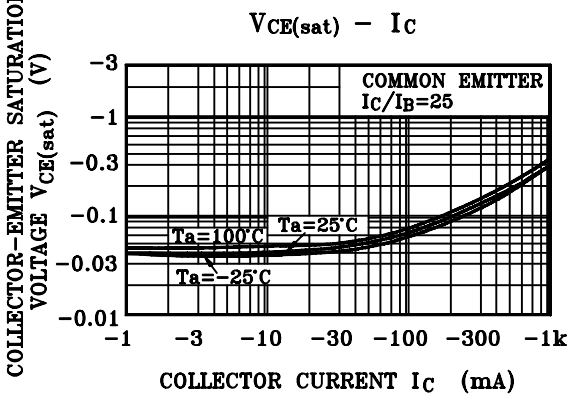
h_{FE} - I_C



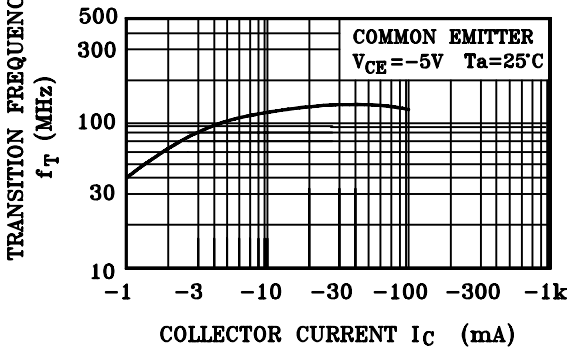
I_C-V_{CE} (LOW VOLTAGE REGION)



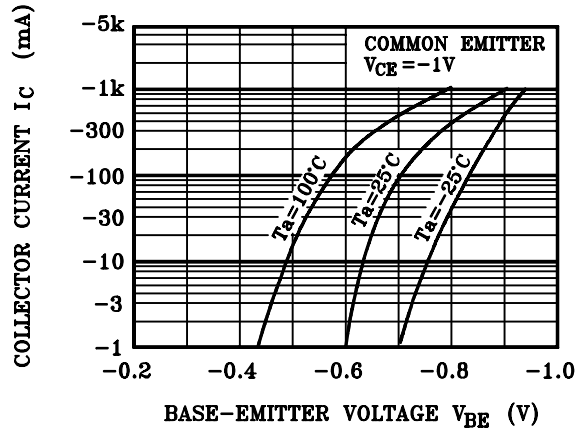
$V_{CE(sat)}$ - I_C



f_T - I_C



I_C - V_{BE}



P_C - Ta